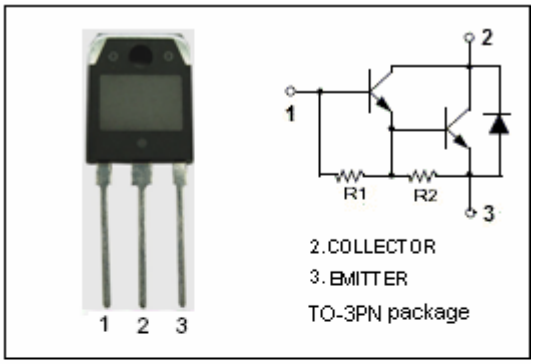
isc Silicon NPN Darlington Power Transistor 2SD2256

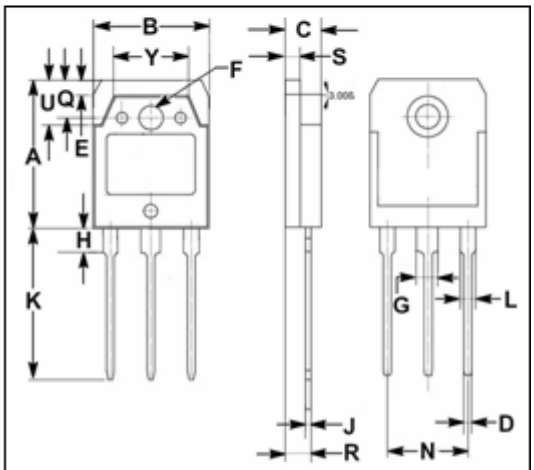


DESCRIPTION

- High DC Current Gain
  : h_{FE}= 2000(Min.)@ I_C= 12A, V_{CE}= 4V
- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$ = 120V(Min)

APPLICATIONS

- Designed for low frequency power amplifier applications.



DIM	mm MIN	mm MAX
A	19.90	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.10
H	3.20	3.40
J	0.595	0.605
K	20.50	20.70
L	1.90	2.10
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	25	A
I_{CM}	Collector Current-Peak	35	A
P_C	Collector Power Dissipation @T_C=25℃	120	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 200mA, R_{BE}= ∞	120			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 0.1mA, I_E= 0	120			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 25mA, R_{BE}= ∞	120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 50mA, I_C= 0	7			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 12A ,I_B= 24mA			2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 25A ,I_B= 250mA			3.5	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 12A ,I_B= 24mA			3.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 25A ,I_B= 250mA			4.5	V
I_{CBO}	Collector Cutoff current	V_{CB}= 100V, I_E= 0			10	μA
I_{CEO}	Collector Cutoff current	V_{CE}= 100V, R_{BE}= ∞			10	μA
h_{FE-1}	DC Current Gain	I_C= 12A ; V_{CE}= 4V	2000		20000	
h_{FE-2}	DC Current Gain	I_C= 25A ; V_{CE}= 4V	500			